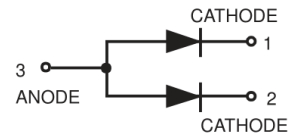
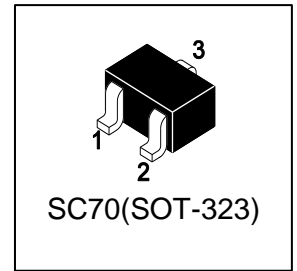


LBAT54AWT1G

S-LBAT54AWT1G

Dual Series Schottky Barrier Diodes



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- Prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBAT54AWT1G	B7	3000/Tape&Reel
LBAT54AWT3G	B7	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse Voltage	VR	30	V
Power Dissipation @ TA = 25°C	PD	200	mW
Derate above 25°C		2	mW/°C
Forward Current(DC)	IF	200	mA
Junction Temperature	TJ	125	°C
Storage Temperature Range	Tstg	-55~+125	°C

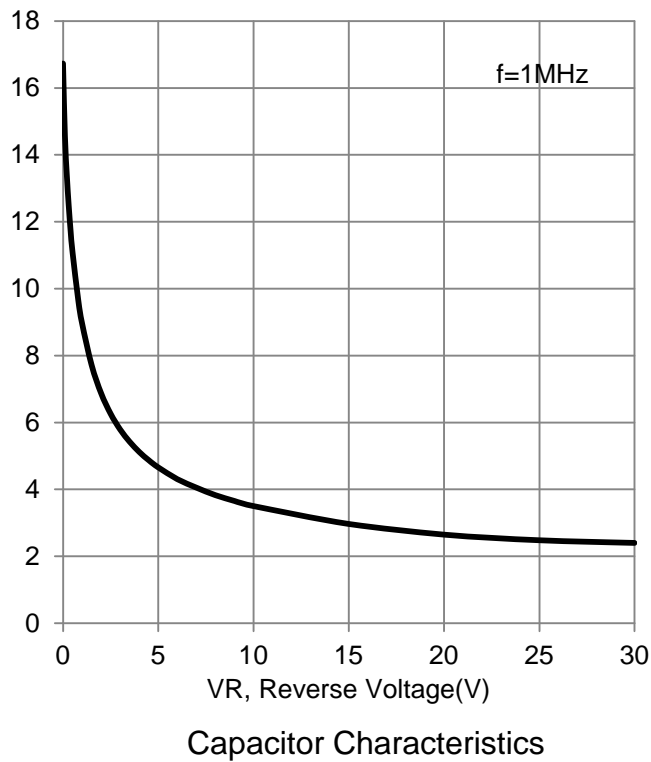
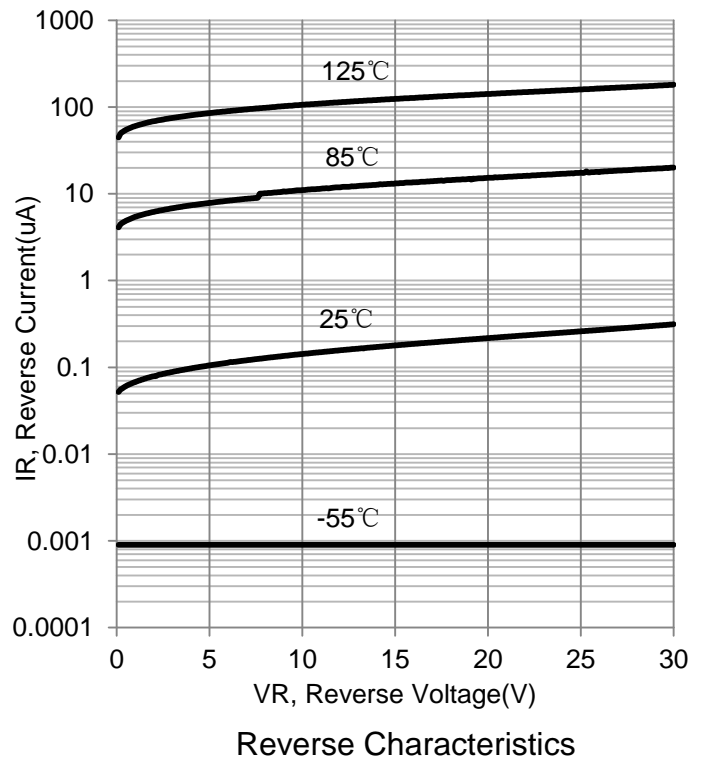
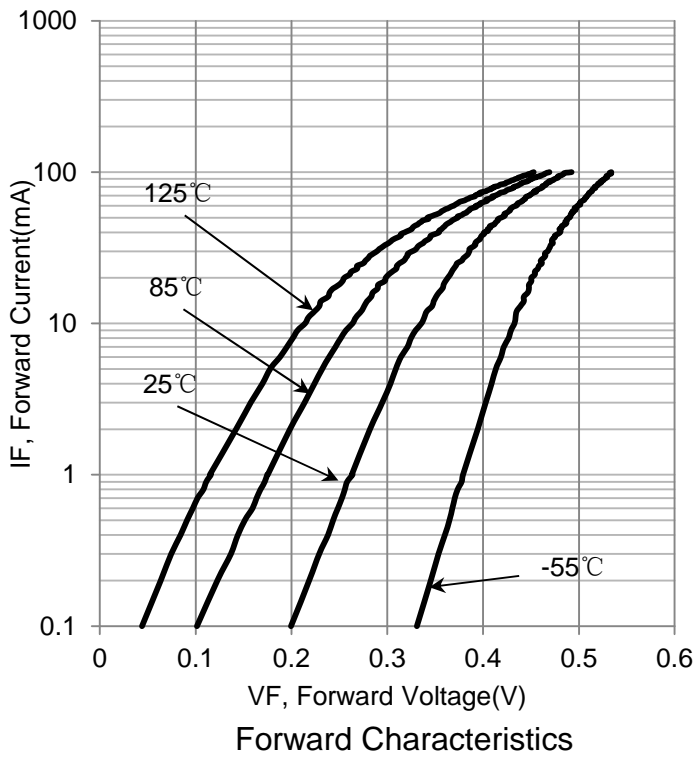
4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Thermal Resistance,Junction-to-Ambient	RθJA	500	°C/W
Thermal Resistance,Junction-to-Case	RθJC	300	°C/W

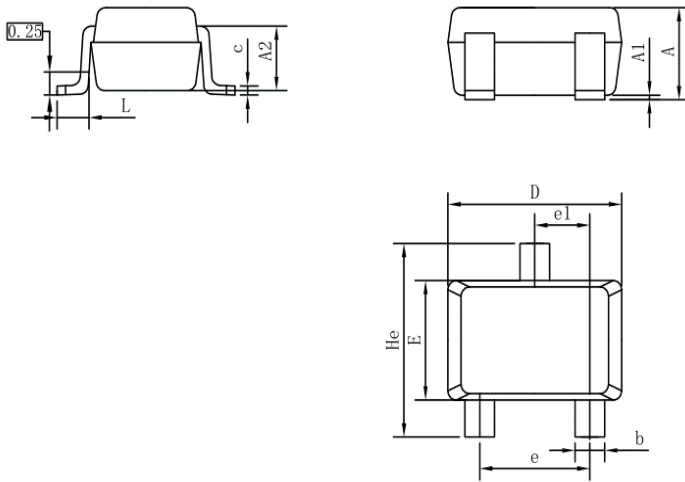
5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage (IR = 10 μA)	V(BR)R	30	-	-	V
Total Capacitance (VR = 1.0 V, f = 1.0 MHz)	CT	-	-	10	pF
Reverse Leakage (VR = 25 V)	IR	-	0.5	2	μA
Forward Voltage (IF = 0.1 mA) (IF = 1.0 mA) (IF = 10 mA) (IF = 30 mA) (IF = 100 mA)	VF	- - - - -	0.22 0.29 0.35 0.41 0.52	0.24 0.32 0.4 0.5 1	V
Reverse Recovery Time (IF = IR = 10 mA, IR(REC) = 1.0 mA)	trr	-	-	5	nS
Forward Current (DC)	IF	-	-	200	mA
Repetitive Peak Forward Current	IFRM	-	-	300	mA
Non-Repetitive Peak Forward Current (t < 1.0 s)	IFSM	-	-	600	mA

6.ELECTRICAL CHARACTERISTICS CURVES

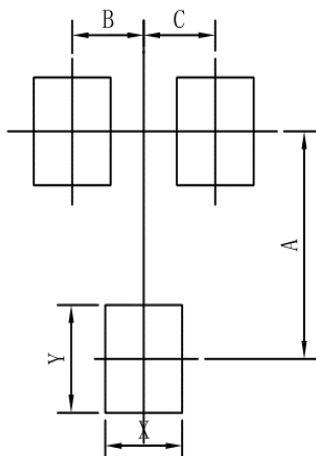


7.OUTLINE AND DIMENSIONS



SC70			
DIM	MIN	NOR	MAX
A	0.80	0.95	1.00
A1	0.00	0.05	0.10
A2	0.7 REF		
b	0.30	0.35	0.40
c	0.10	0.15	0.25
D	1.80	2.05	2.20
E	1.15	1.30	1.35
e	1.20	1.30	1.40
e1	0.65 BSC		
L	0.20	0.35	0.56
He	2.00	2.10	2.40
ALL Dimension in mm			

8.SOLDERING FOOTPRINT



SC70	
DIM	MIN
A	1.90
B	0.65
C	0.65
X	0.70
Y	0.90

单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)